

1.0 SCOPE

This specification documents the detail requirements for space qualified die manufactured on Analog Devices, Inc.'s QML certified line per MIL-PRF-38534 class K except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at <http://www.analog.com/aerospace> is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete datasheet for commercial product grades can be found at www.analog.com/AMP01

2.0 Part Number. The complete part number(s) of this specification follow:

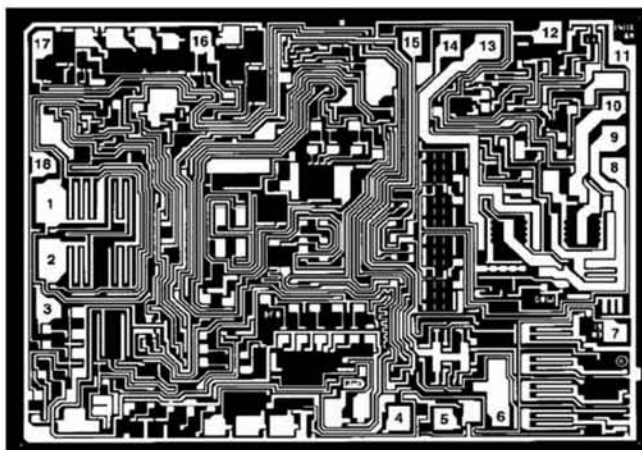
<u>Part Number</u>	<u>Description</u>
AMP01-000C	Low-Noise Precision Instrumentation Amplifier

3.0 Die Information

3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization
111 mil x 149 mil	19 mil $\pm$ 2 mil	Al/Cu

3.2 Die Picture



- | | |
|-------------------|--------------------|
| 1. R_G | 10. V_- (OUTPUT) |
| 2. R_G | 11. V_- |
| 3. $-INPUT$ | 12. V_+ |
| 4. V_{OOS} NULL | 13. V_+ (OUTPUT) |
| 5. V_{OOS} NULL | 14. R_S |
| 6. TEST PIN* | 15. R_S |
| 7. SENSE | 16. V_{IOS} NULL |
| 8. REFERENCE | 17. V_{IOS} NULL |
| 9. OUTPUT | 18. $+INPUT$ |

Make no electrical connection to unlabeled pads.

3.3 Absolute Maximum Ratings 1/

Supply Voltage (V_S)	$\pm 18V$ dc
Common Mode Input Voltage	Supply Voltage
Differential Input Voltage:	
$R_G \geq 2k\Omega$	$\pm 20V$ dc
$R_G < 2k\Omega$	$\pm 10V$ dc
Output Short Circuit Duration	Indefinite
Storage Temperature Range	$-65^\circ C$ to $+150^\circ C$
Ambient Operating Temperature Range	$-55^\circ C$ to $+125^\circ C$

Absolute Maximum Ratings Notes:

1. Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

4.0 Die Qualification

In accordance with class-K version of Mil-Prf-38534, Appendix C, Table C-II, except as modified herein.

(a) Qual Samples Size and Qual Acceptance Criteria – 25/2

(b) Qual Sample Package – DIP

(c) Pre-screen test post assembly required prior to die qualification, to remove all assembly related rejects.

Table I - Dice Electrical Characteristics

Parameter	Symbol	Conditions <u>1/</u>		Limit Min	Limit Max	Units
Input Bias Current	I_B				± 4	nA
Input Offset Current	I_{IO}				1	nA
Offset Referred to Input vs. Positive Supply	+PSR	$V_+ = +5V$ to $+15V$, $V_- = -15V$	$G = 1000$	120		dB
			$G = 100$	110		
			$G = 10$	95		
			$G = 1$	75		
Offset Referred to Input vs. Negative Supply	-PSR	$V_- = -5V$ to $-15V$ $V_+ = +15V$	$G = 1000$	105		dB
			$G = 100$	90		
			$G = 10$	70		
			$G = 1$	50		
Input Voltage Range	IVR			± 10		V

Table I - Dice Electrical Characteristics (Continued)					
Parameter	Symbol	Conditions <u>1/</u>	Limit Min	Limit Max	Units
Common Mode Rejection	CMR	$V_{CM} = I_{VR}$	$G = 1000$	125	dB
			$G = 100$	120	
			$G = 10$	100	
			$G = 1$	85	
Gain Equation Accuracy	GE	$G = 20R_S/R_G$		0.8	%
Output Short Circuit Current	I_{OS+}		60	120	mA
	I_{OS-}		-120	-60	
Reference Input Resistance	R_{INREF}		35	65	k Ω
Quiescent Current	I_Q	+V Linked to +V _{OP} -V Linked to -V _{OP}		4.8	mA
Input Offset Voltage	V_{IOS}			120	μ V
Output Offset Voltage	V_{OOS}			4	mV
Output Voltage Swing	V_O	$R_L = 2k\Omega$	± 13		V
		$R_L = 500\Omega$	± 13		
		$R_L = 50\Omega$	± 2.5		

Table I Notes:

1. $V_S = \pm 15V$, $R_S = 10k\Omega$, $R_L = 2k\Omega$, $T_A = 25^\circ C$, unless otherwise specified.

Table II - Electrical Characteristics for Qual Samples

Table II - Electrical Characteristics for Qual Samples							
Parameter	Symbol	Conditions 1/		Sub- groups	Limit Min	Limit Max	Units
Input Bias Current	I _B			1		±4	nA
				2, 3		±10	
Input Offset Current	I _{IO}			1		1	nA
				2, 3		3	
Input Voltage Range	IVR			1, 2, 3	±10V		V
Offset Referred to Input vs. Positive Supply	+PSR	V+ = +5V to +15V, V- =-15V	G = 1000	1, 2, 3	120		dB
			G = 100		110		
			G = 10		95		
			G = 1		75		
Offset Referred to Input vs. Negative Supply	-PSR	V- = -5V to - 15V, V+ = +15V	G = 1000	1, 2, 3	105		dB
			G = 100		90		
			G = 10		70		
			G = 1		50		
Common Mode Rejection	CMR	V _{CM} = IVR, 1kΩ Source Imbalance	G = 1000	1	125		dB
				2, 3	120		
			G = 100	1	120		
				2, 3	115		
			G = 10	1	100		
				2, 3	95		
			G = 1	1	85		
				2, 3	80		
Gain Equation Accuracy	GE	2/		1		0.8	%
Gain Range	G			1	1	1000	V/V
Output Short Circuit Current	I _{OS} +			1	60	120	mA
	I _{OS} -				-120	-60	
Reference Input Resistance	R _{INREF}			1	35	65	kΩ
Quiescent Current	I _Q	+V Linked to +V _{OP} -V Linked to -V _{OP}		1		4.8	mA
Input Offset Voltage	V _{IOS}			4		120	μV
				5, 6		170	
Output Offset Voltage	V _{OOS}			4		6	mV
				5, 6		10	
Output Offset Voltage Drift	TCV _{OOS}	R _G = ∞		8		50	μV/°C
Output Voltage Swing	V _O	R _L = 500Ω, 2kΩ		4	±13		V
				5, 6	±12		
		R _L = 50Ω		4	±2.5		

Table II - Electrical Characteristics for Qual Samples (Continued)						
Parameter	Symbol	Conditions <u>1/</u>	Sub- groups	Limit Min	Limit Max	Units
Average Input Offset Voltage Drift	TCV _{IOS}	T _A = -55°C, +125°C	8	1.0		μV/°C

Table II Notes:

1. V_S = ±15V, R_S = 100Ω, R_L = 2kΩ, unless otherwise specified.
2. G = 20R_S/R_G, accuracy measured at G = 1, 10, 100, and 1000.

Table III - Life Test Endpoint and Delta Parameter (Product is tested in accordance with Table II with the following exceptions)								
Parameter	Symbol	Sub- groups	Burn In Limit Min	Burn In Limit Max	Life Test Limit Min	Life Test Limit Max	Life Test Delta	Units
Input Offset Voltage	V _{IOS}	4		160		200	±40	μV
		5, 6				250		
Output Offset Voltage	V _{OOS}	4		10		16	±6	mV
		5, 6				20		
Input Bias Current	I _B	1		±7		±10	±3	nA
		2, 3				±16		

5.0 Life Test/Burn-In Information

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	25-Sep-07
B	Update web address	Jan. 25, 2002
C	Update web address	Aug. 5, 2003